

TF2183(4)M

Half-Bridge Gate Driver

Features

- Floating high-side driver in bootstrap operation to 600V
- Drives two N-channel MOSFETs or IGBTs in a half bridge configuration
- 1.9A source / 2.3A sink output current capability
- Outputs tolerant to negative transients
- Internal dead time of 400ns to protect MOSFETs
- Wide low side gate driver supply voltage: 10V to 20V
- Logic input (HIN and LIN*) 3.3V capability
- Schmitt triggered logic inputs with internal pull down
- Undervoltage lockout for high and low side drivers
- Extended temperature range: -40°C to +125°C

Applications

- DC-DC Converters
- AC-DC Inverters
- Class D Power Amplifiers

Typical Application

Motor Controls

Up to 600V

PART NUMBER	PACKAGE	PACK / Qty	MARK
TF2183M-TAU	SOIC-8	Tube / 100	TF2183M
TF2183M-TAH	SOIC-8	T&R / 2500	Lot ID
TF21834M-TUU	SOIC-14	Tube / 100	TF21834M
TF21834M-TUH	SOIC-14	T&R / 2500	Lot ID

Description

The TF2183(4)M is a high voltage, high speed gate driver capable of driving N-channel MOSFETs and IGBTs in a half bridge configuration. TF Semiconductor's high voltage process enables the TF2183(4)M's high side to switch to 600V in a bootstrap operation.

The TF2183(4)M logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with controlling devices. The driver outputs feature high pulse current buffers designed for minimum driver cross conduction. TF2183(4)M has a fixed internal deadtime of 400ns (typical).

The TF2183M is offered in an SOIC-8(N) package and the TF21834M is offered in an SOIC-14(N) package and operates over an extended -40 °C to +125 °C temperature range.





SOIC-8(N)

Ordering Information

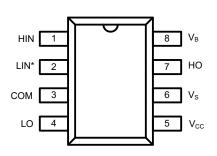
Year Year Week Week

	₩			=
V _{CC} O HIN O LIN* O	V _{cc} HIN LIN* TF2183M COM	HO Vs LO		TO LOAD

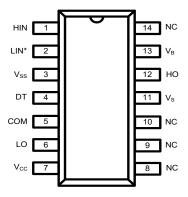
www.tfsemi.com Rev. 1.0







Top View: SOIC-8 **TF2183M**



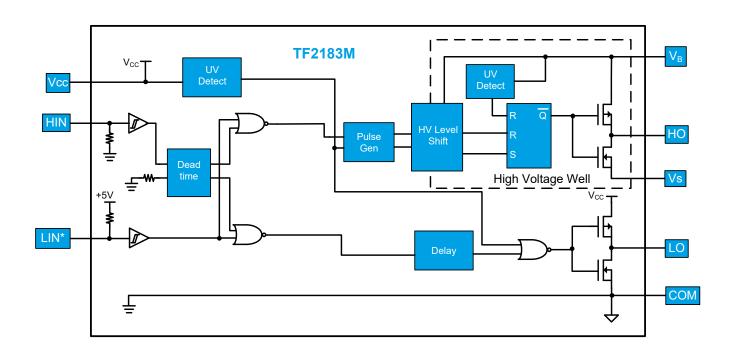
Top View: SOIC-14 **TF21834M**

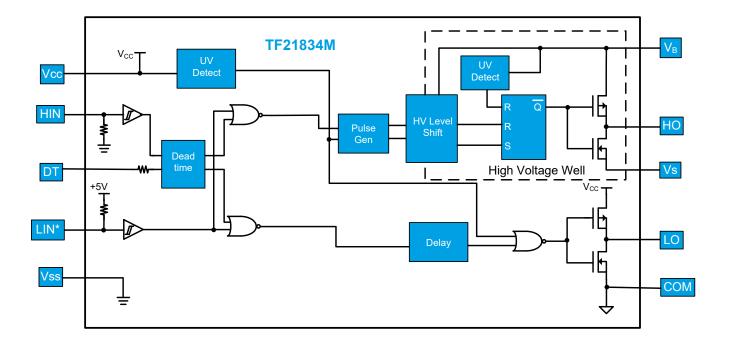
Pin Descriptions

PIN NAME	TF2183M Pin	TF21834M Pin	PIN DESCRIPTION	
HIN	1	1	Logic input for high-side gate driver, in phase with HO.	
LIN*	2	2	Logic input for low-side gate driver, out of phase with LO.	
СОМ	3	5	Low-side and logic return (TF2183M).	
LO	4	6	Low-side gate drive output.	
V _{cc}	5	7	Low-side and logic fixed supply.	
V _s	6	11	High-side floating supply return.	
НО	7	12	High-side gate drive output.	
V _B	8	13	High-side floating supply.	
V _{ss}		3	Logic return.	
DT		4	Programmable deadtime lead, set by external resistor to VSS.	



Functional Block Diagrams







Half-Bridge Gate Driver

Absolute Maximum Ratings (NOTE1)

V _B - High side floating supply voltage	0.3V to +624V
V _s - High side floating supply offset voltag	eV_B -24V to V_B +0.3V
V _{HO} -High side floating output voltage	V_s -0.3V to V_B +0.3V
dV _s /dt-Offset supply voltage transient	50 V/ns
3	
V _{cc} - Low-side fixed supply voltage	0.3V to +24V
V ₁₀ - Low-side output voltage	0.3V to V _{cc} +0.3V
V _{IN} - Logic input voltage (HIN and LIN*)	0.3V to V = +0.3V

NOTE1 Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

P_D - Package power dissipation at $T_A \le 25$ °C SOIC-8	0.625W
SOIC-14	
SOIC-8(N) Thermal Resistance (NOTE2)	
$ heta_{JA}$	200 °C/W
SOIC-14(N) Thermal Resistance (NOTE2)	
θ _{JA}	120 °C/W
T ₁ - Junction operating temperature	+150 °C
T _L - Lead Temperature (soldering, 10 seconds)	+300°C
T _{stg} - Storage temerature	55 to 150 °C

NOTE2 When mounted on a standard JEDEC 2-layer FR-4 board.

Recommended Operating Conditions

Symbol	Parameter	MIN	MAX	Unit
V _B	High side floating supply absolute voltage	V _s + 10	V _s + 20	
V _s	High side floating supply offset voltage	NOTE3	600	
V _{HO}	High side floating output voltage	V _s	V _B	
V _{cc}	Low side fixed supply voltage	10	20	V
V _{LO}	Low side output voltage	0	V _{cc}	
V _{IN}	Logic input voltage (HIN and LIN*)	0	5	
V _{DT}	Programmable deadtime pin voltage	V _{ss}	V _{cc}	
V _{ss}	Logic ground (referenced to COM)	-5	5	
T _A	Ambient temperature	-40	125	°C

NOTE3 Logic operational for VS of -5V to +600V.

DC Electrical Characteristics (NOTE4)

 $\rm V_{BIAS} \, (V_{CC}, V_{BS} \,) = 15V, T_A = 25 \, ^{\circ} C$, unless otherwise specified.

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit
V _{IH}	Logic "1" (HIN) and logic "0" (LIN*) input voltage	V _{cc} = 10V to 20V	2.5			
V _{IL}	Logic "0" (HIN) and logic "1" (LIN*) input voltage	NOTE5			0.8	V
V _{OH}	High level output voltage, V _{BIAS} - V _O	$I_{O} = 0A$			1.2	V
V _{OL}	Low level output voltage, V _o	I _o = 20mA			0.1	
I _{LK}	Offset supply leakage current	VB = VS = 600V			50	
I _{BSQ}	Quiescent V _{BS} supply current	V _{IN} = 0V or 5V	20	60	150	μΑ
I _{ccq}	Quiescent V _{CC} supply current	V _{IN} = 0V or 5V	0.4	1.6	2.0	mA
I _{IN+}	Logic "1" input bias current	HIN = 5V, LIN* = 0V		25	60	
I _{IN-}	Logic "0" input bias current	HIN = 0V, LIN* = 5V			1.0	μΑ
V_{BSUV}	V _{BS} supply under-voltage positive going threshold		8.0	8.9	9.8	
V _{BSUV} -	V _{BS} supply under-voltage negative going threshold		7.4	8.2	9.0	V
V_{CCUV+}	V _{CC} supply under-voltage positive going threshold		8.0	8.9	9.8	
V _{CCUV} -	V _{cc} supply under-voltage negative going threshold		7.4	8.2	9.0	
I _{O+}	Output high short circuit pulsed current	$V_O = 0V$, PW $\leq 10 \mu s$	1.4	1.9		
I ₀₋	Output low short circuit pulsed current	$V_0 = 15V, PW \le 10 \mu s$	1.7	2.3		A

NOTE4 The V_{IN} , V_{TI} , and I_{IN} parameters are applicable to the two logic input pins: HIN and LIN*. The V_{O} and I_{O} parameters are applicable to the respective output pins: HO and LO **NOTE5** For optimal operation, it is recommended that the input pulse (to HIN and LIN*) should have an amplitude of 2.5V minimum with a pulse width of 800ns minimum.



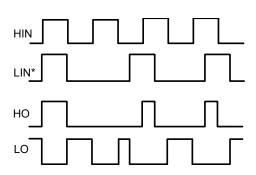


AC Electrical Characteristics

 $V_{BIAS}(V_{CC},V_{BS})=15V,C_{L}=1000 pF,$ and $T_{A}=25~^{\circ}C$, unless otherwise specified.

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit
t _{on}	Turn-on propogation delay	$V_s = 0V$		180	270	
t _{off}	Turn-off propogation delay	V _s = 0V or 600V		220	330	
t _{DM}	Delay matching				50	
t _r	Turn-on rise time			40	60	ns
t _f	Turn-off fall time			20	35	
		$R_{DT} = 0\Omega$	280	400	520	
t _{DT}	Deadtime: t _{DT LO-HO} & t _{DT HO-LO}	$R_{DT} = 200 k\Omega \text{ (TF21834)}$	4	5	6	μs
		$R_{DT} = 0\Omega$		0	50	
t _{DTM}	Deadtime matching: t _{DT LO-HO} - t _{DT HO-LO}	$R_{DT} = 200 k\Omega \text{ (TF21834)}$		0	600	ns

Timing Waveforms





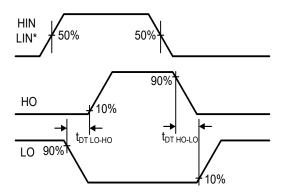


Figure 2. Deadtime Waveform Definitions

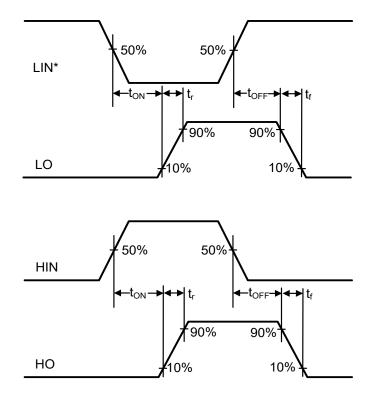
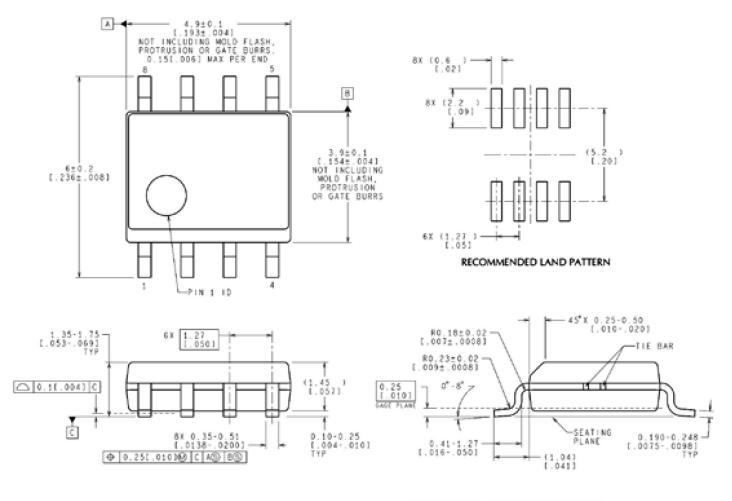


Figure 3. Switching Time Waveform Definitions



Package Dimensions (SOIC-8 N)

Please contact support@tfsemi.com for package availability.



NOTES: UNLESS OTHERWISE SPECIFIED

1. REFERENCE JEDEC REGISTRATION MS-012, VARIATION AA.

CONTROLLING DIMENSION IS MILLIMETER
VALUES IN [] ARE INCHES
DIMENSIONS IN () FOR REFERENCE ONLY





Revision History

Rev.	Change	Owner	Date
1.0	First release, AI datasheet	Keith Spaulding	7/15/2022

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